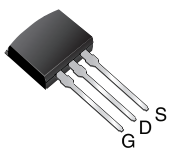
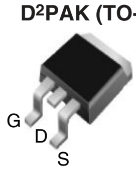
Power MOSFET

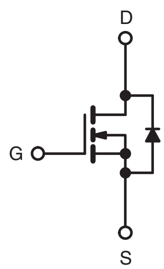
PRODUCT SUMMARY		
V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.018
Q_g (Max.) (nC)	110	
Q_{gs} (nC)	29	
Q_{gd} (nC)	36	
Configuration	Single	

I2PAK (TO-262)



D2PAK (TO-263)





N-Channel MOSFET

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Advanced Process Technology
- Dynamic dV/dt
- 175 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Drop in Replacement of the IRFZ48, SiHFZ48 for Linear/Audio Applications
- Compliant to RoHS Directive 2002/95/EC

RoHS*
COMPLIANT
HALOGEN FREE Available

DESCRIPTION

Advanced Power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D2PAK is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D2PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2 W in a typical surface mount application.

ORDERING INFORMATION		
Package	D2PAK (TO-263)	I2PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHFZ48RS-GE3	-
Lead (Pb)-free	IRFZ48RSPbF	IRFZ48RLPbF
	SiHFZ48RS-E3	SiHFZ48RL-E3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	60	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current[e]	V_{GS} at 10 V	T_C = 25 °C	I_D	50	A
		T_C = 100 °C		50	
Pulsed Drain Current[a, e]			I_{DM}	290	
Linear Derating Factor				1.3	W/°C
Single Pulse Avalanche Energy[b, e]			E_{AS}	100	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	190	W
Peak Diode Recovery dV/dt[c, e]			dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)[d]	for 10 s			300[d]	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = 25 V, Starting T_J = 25 °C, L = 22 μH, R_g = 25 Ω, I_{AS} = 72 A (see fig. 12).
c. $I_{SD} \leq 72$ A, dI/dt ≤ 200 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
d. 1.6 mm from case.
e. Current limited by the package, (die current = 72 A).

* Pb containing terminations are not RoHS compliant, exemptions may apply

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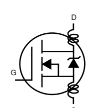
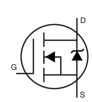
THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.8	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA[c]	-	0.60	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V	-	-	25	μA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 150 °C	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 43 A[b]	-	-	0.018	Ω
Forward Transconductance	g_{fs}	V_{DS} = 25 V, I_D = 43 A[b]	27	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5[c]	-	2400	-	pF
Output Capacitance	C_{oss}		-	1300	-	
Reverse Transfer Capacitance	C_{rss}		-	190	-	
Total Gate Charge	Q_g	V_{GS} = 10 V, I_D = 72 A, V_{DS} = 48 V, see fig. 6 and 13[b, c]	-	-	110	nC
Gate-Source Charge	Q_{gs}		-	-	29	
Gate-Drain Charge	Q_{gd}		-	-	36	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 30 V, I_D = 72 A, R_g = 9.1 Ω, R_D = 0.34 Ω, see fig. 10[b, c]	-	8.1	-	ns
Rise Time	t_r		-	250	-	
Turn-Off Delay Time	$t_{d(off)}$		-	210	-	
Fall Time	t_f		-	250	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	50[c]	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	290	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 72 A, V_{GS} = 0 V[b]	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 72 A, dI/dt = 100 A/μs[b, c]	-	120	180	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.50	0.80	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.
c. Current limited by the package, (die current = 72 A).

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

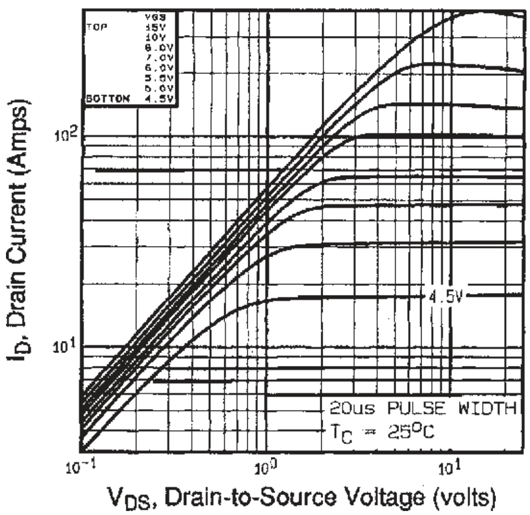

Fig. 1 - Typical Output Characteristics

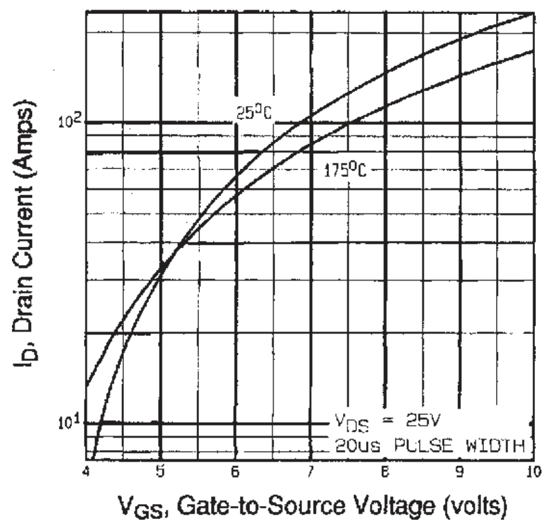

Fig. 3 - Typical Transfer Characteristics

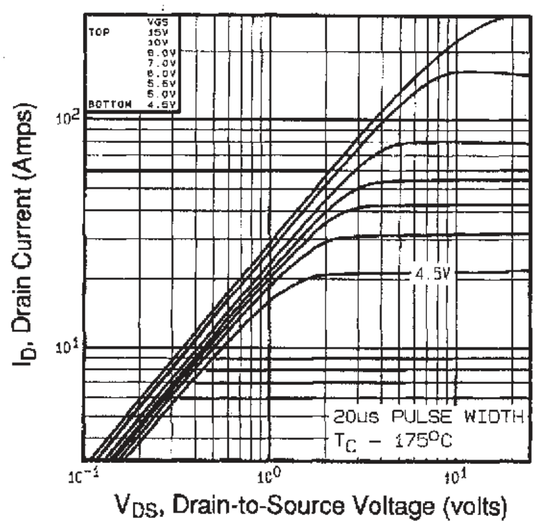

Fig. 2 - Typical Output Characteristics

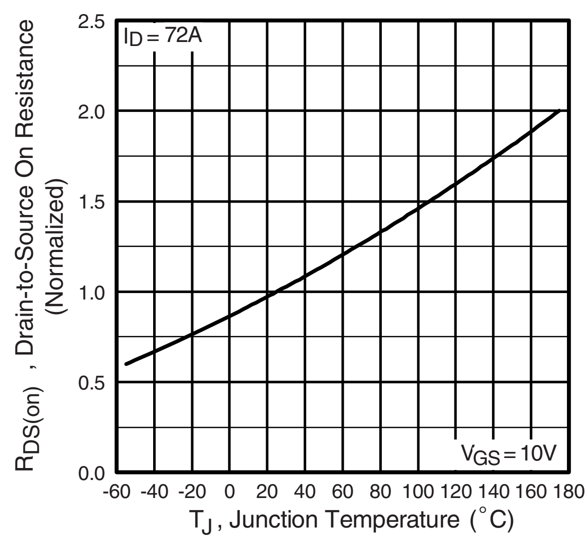

Fig. 4 - Normalized On-Resistance vs. Temperature

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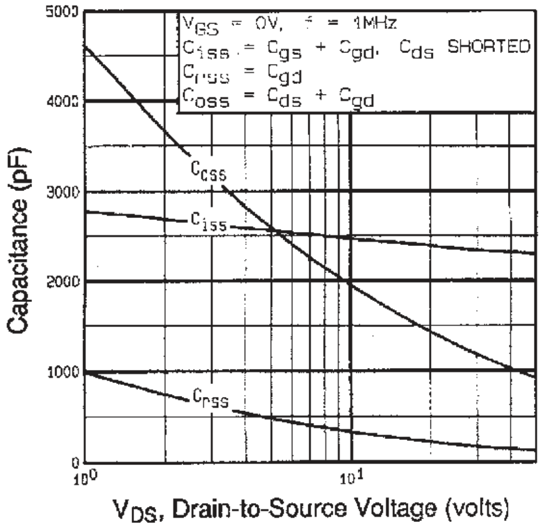

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

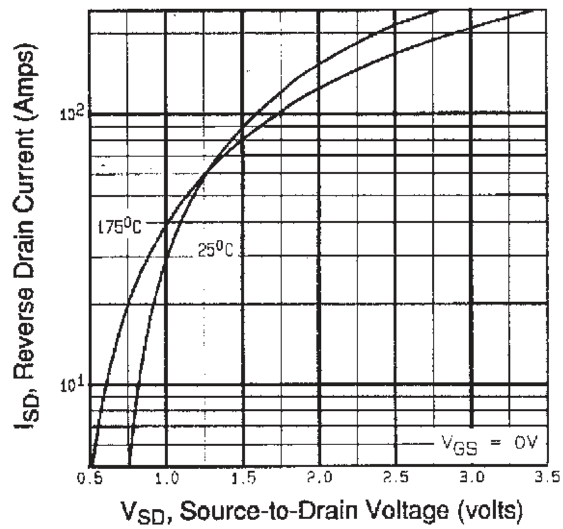

Fig. 7 - Typical Source-Drain Diode Forward Voltage

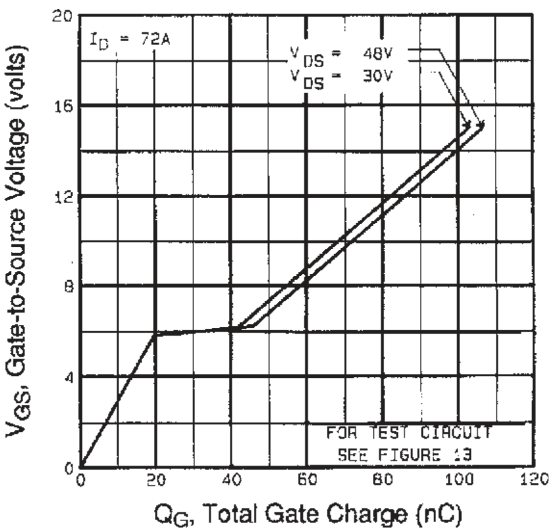

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

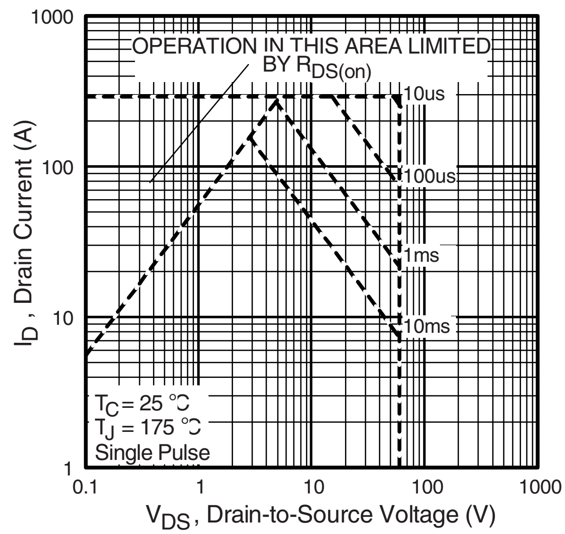

Fig. 8 - Maximum Safe Operating Area

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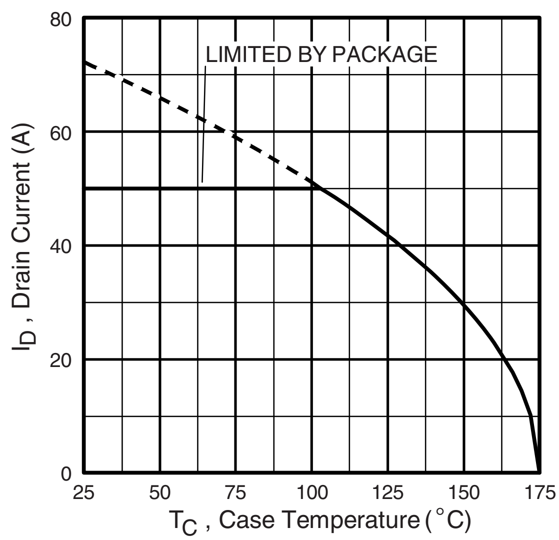

Fig. 9 - Maximum Drain Current vs. Case Temperature

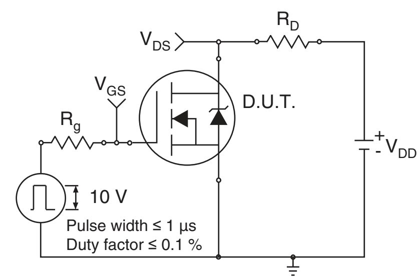

Fig. 10a - Switching Time Test Circuit

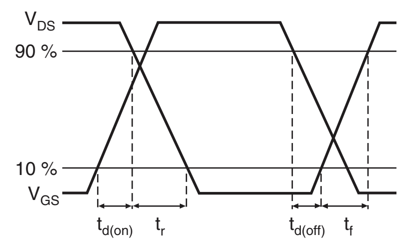

Fig. 10b - Switching Time Waveforms

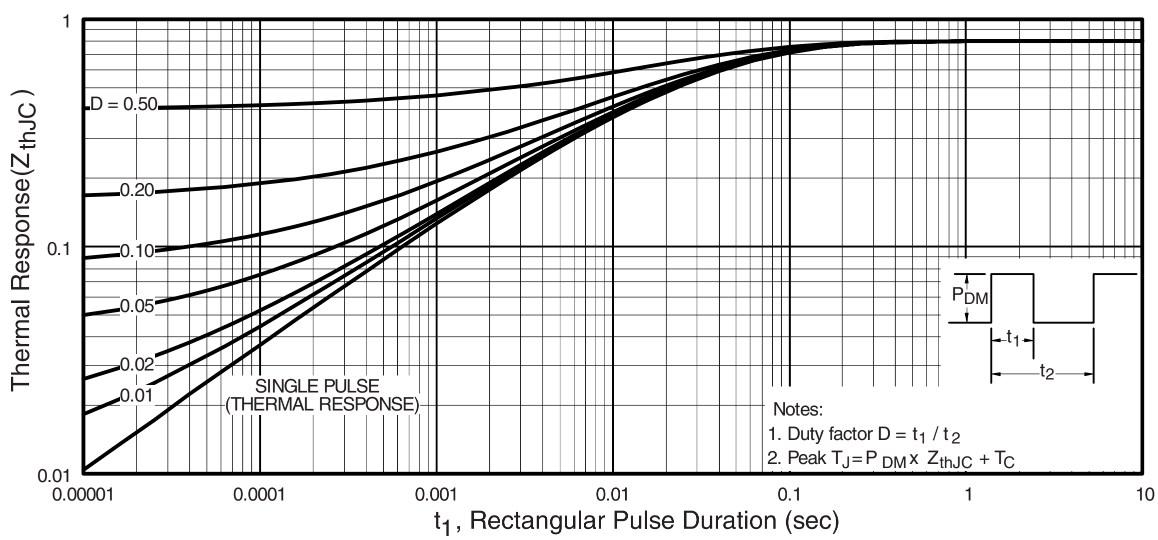

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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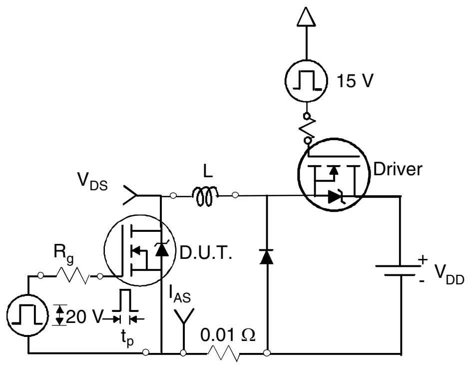

Fig. 12a - Unclamped Inductive Test Circuit

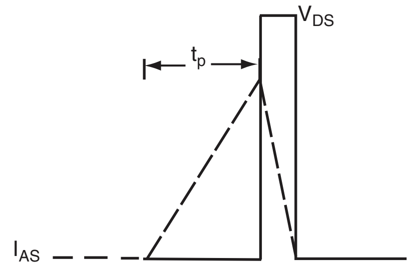

Fig. 12b - Unclamped Inductive Waveforms

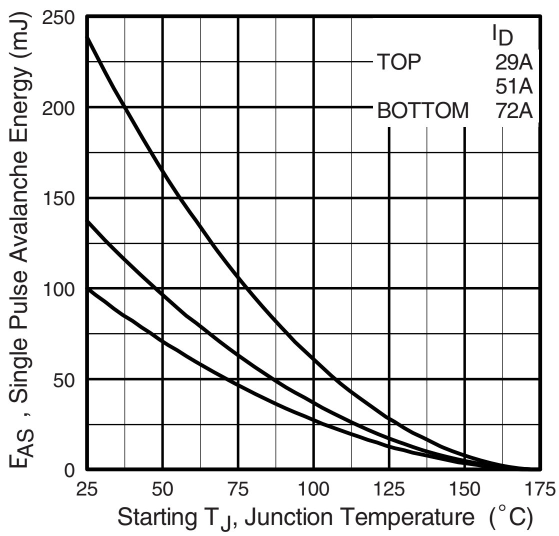

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

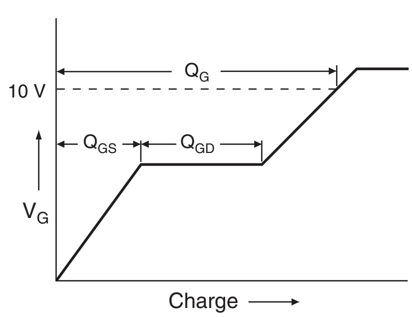

Fig. 13a - Maximum Avalanche Energy vs. Drain Current

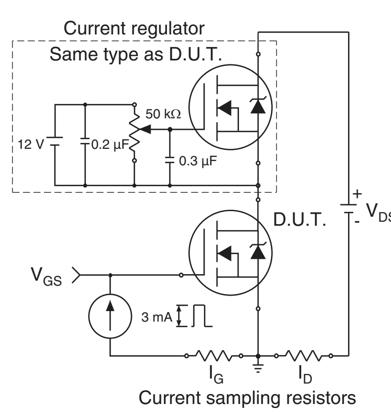

Fig. 13b - Gate Charge Test Circuit

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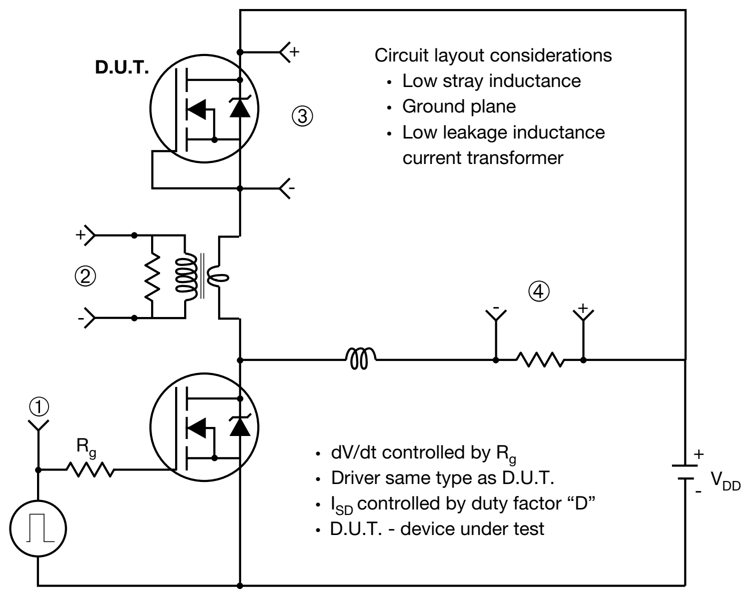
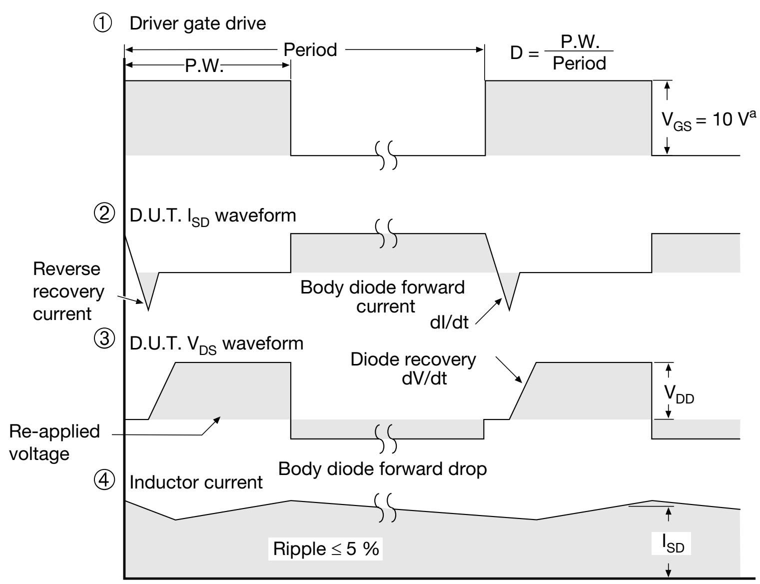
Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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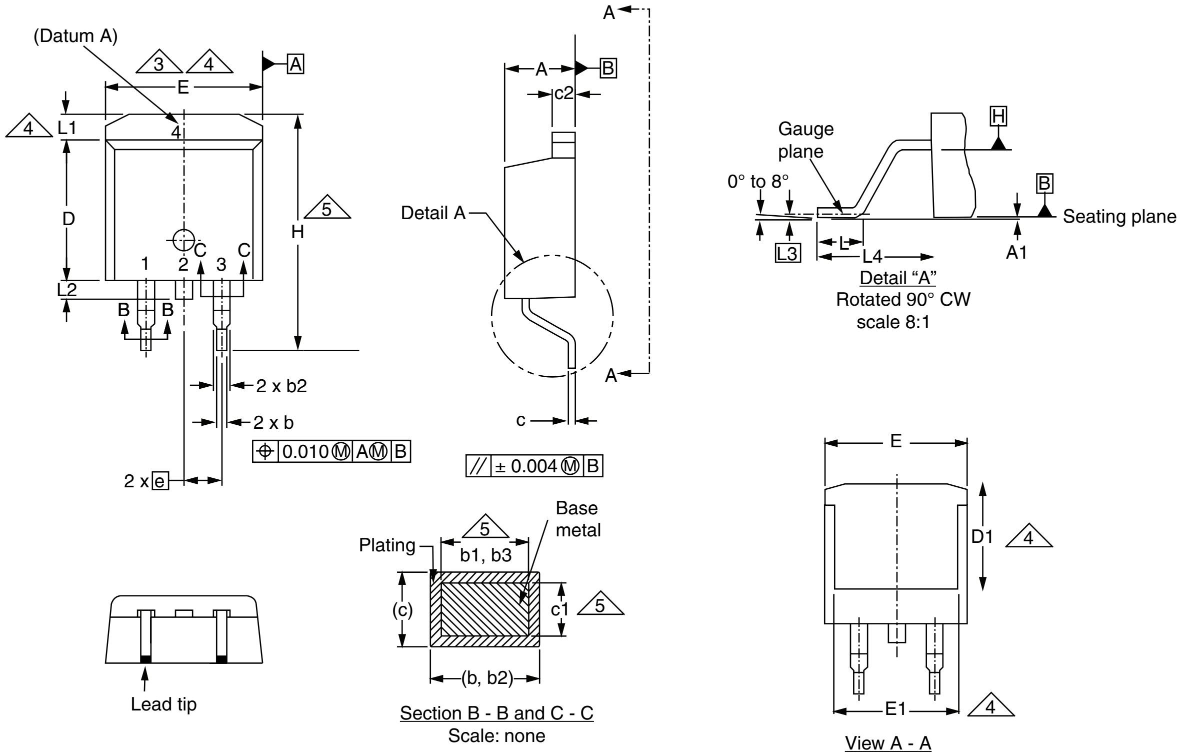
TO-263AB (HIGH VOLTAGE)

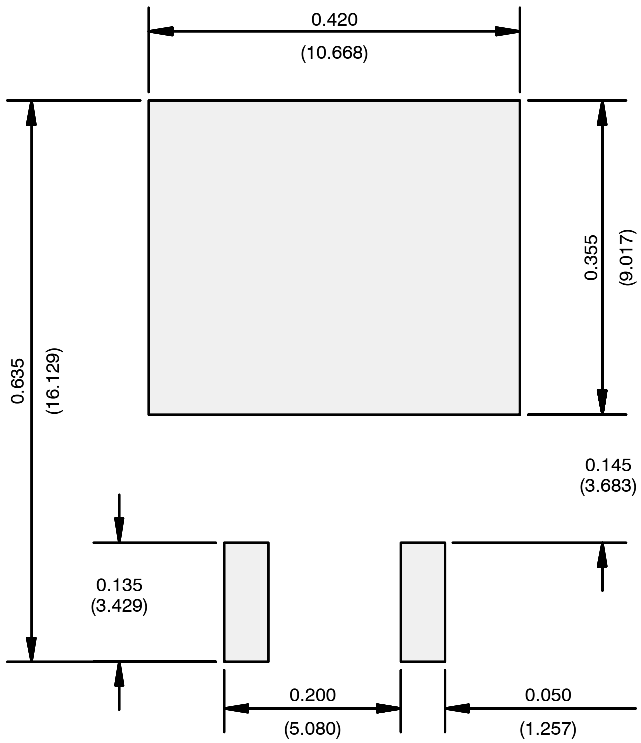


	MILLIMETERS		INCHES			MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.	DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190	D1	6.86	-	0.270	-
A1	0.00	0.25	0.000	0.010	E	9.65	10.67	0.380	0.420
b	0.51	0.99	0.020	0.039	E1	6.22	-	0.245	-
b1	0.51	0.89	0.020	0.035	e	2.54 BSC		0.100 BSC	
b2	1.14	1.78	0.045	0.070	H	14.61	15.88	0.575	0.625
b3	1.14	1.73	0.045	0.068	L	1.78	2.79	0.070	0.110
c	0.38	0.74	0.015	0.029	L1	-	1.65	-	0.066
c1	0.38	0.58	0.015	0.023	L2	-	1.78	-	0.070
c2	1.14	1.65	0.045	0.065	L3	0.25 BSC		0.010 BSC	
D	8.38	9.65	0.330	0.380	L4	4.78	5.28	0.188	0.208
ECN: S-82110-Rev. A, 15-Sep-08 DWG: 5970									

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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